AMENDMENTS TO THE SPECIFICATION

Please replace the paragraph on page 36, lines 15-19 with the following amended paragraph:

When it is assumed that the mutual conductance per unit gate voltage is β21, the ON resistance ~~R21~~ Ron21 of the MOS-FET 21 is obtained by substituting Vgs21 in Vgs of the equation (4), as represented by equation (10).

Please replace the paragraph on page 58, lines 14-26 with the following amended paragraph:

In the equation (27), R50 is the resistance value of the resistor 50, and β35 and β36 are the mutual conductance values per unit gate voltage of the MOS-FETs 35 and 36, respectively. In the MOS-FETs 35 and 36, a relationship of $\beta \propto (W/L)$ is established, as explained according to the equation (18) in the descriptions of the above-mentioned third embodiment. It is thus found that the output voltage V55 is proportional to the channel ~~width~~ widths W, provided that the channel lengths L are the same. Since the power source voltage Vdd is included in the numerator of the equation (27), the output power source voltage V55 is proportional to the power source voltage Vdd.